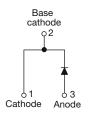


# HEXFRED® Ultrafast Soft Recovery Diode, 8 A





PRIMARY CHARACTERISTICS									
I <sub>F(AV)</sub>	8 A								
V <sub>R</sub>	1200 V								
V <sub>F</sub> at I <sub>F</sub>	2.4 V								
t <sub>rr</sub> typ.	28 ns								
T <sub>J</sub> max.	150 °C								
Package	TO-220AC 2L								
Circuit configuration	Single								

#### **FEATURES**

- · Ultrafast and ultrasoft recovery
- Very low I<sub>RBM</sub> and Q<sub>rr</sub>
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



ROHS COMPLIANT HALOGEN FREE

#### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA08TB120 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08TB120 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the to portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB120 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Cathode to anode voltage	$V_{R}$		1200	V						
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	8							
Single pulse forward current	I <sub>FSM</sub>		130	Α						
Maximum repetitive forward current	I <sub>FRM</sub>		32							
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	73.5	W						
Maximum power dissipation	r <sub>D</sub>	T <sub>C</sub> = 100 °C	29	VV						
Operating junction and storage temperature range	$T_J$ , $T_{Stg}$		-55 to +150	°C						



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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V <sub>BR</sub>	Ι <sub>R</sub> = 100 μΑ	1200	-	-				
Maximum forward voltage		I <sub>F</sub> = 8.0 A -		2.6	3.3	V			
	$V_{FM}$	I <sub>F</sub> = 16 A	-	3.4	4.3				
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 125 °C	-	2.4	3.1				
Maximum reverse		$V_R = V_R$ rated	-	0.31	10				
leakage current	I <sub>RM</sub>	T <sub>J</sub> = 125 °C, V <sub>R</sub> = 0.8 x V <sub>R</sub> rated	-	135	1000	μA			
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	11	20	pF			
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS				
Reverse recovery time	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	$A/\mu s$ , $V_R = 30 V$	-	28	-	ns			
	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	63	95				
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	106	160				
Deal, see assess as suggest	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.5	8.0	A nC A/μs			
Peak recovery current	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C	$I_F = 8.0 A$ $dI_F/dt = 200 A/\mu s$	-	6.2	11				
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	$V_{R} = 200 \text{ V}$	-	140	380				
Reverse recovery charge	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	335	880				
Peak rate of recovery current during t <sub>b</sub>	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	133	-				
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	85	-				

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	1.7				
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	40	K/W			
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.25	-				
Weight			-	6.0	-	g			
vveigni			-	0.21	-	OZ.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style 2L TO-220AC	HFA08TB120						

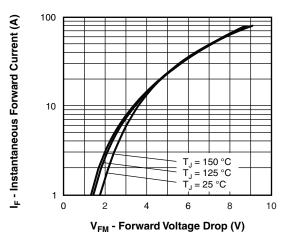


Fig. 1 - Maximum Forward Voltage Drop Characteristics

Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

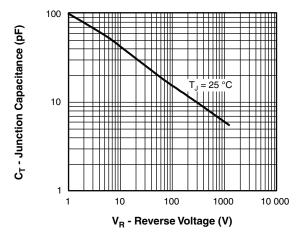


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

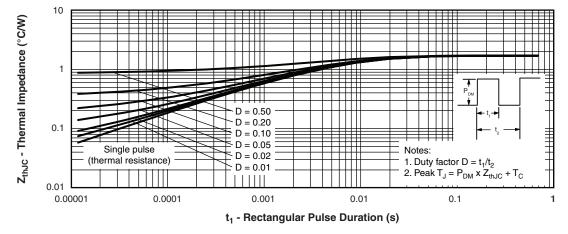


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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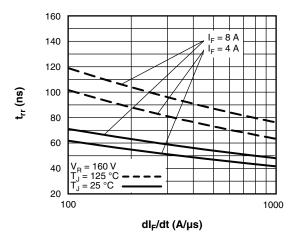
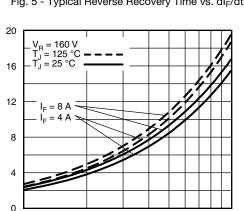


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt



dI<sub>F</sub>/dt (A/µs) Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

100

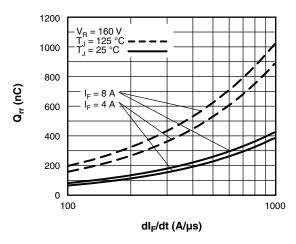


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

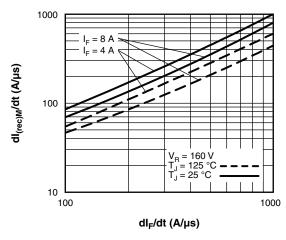
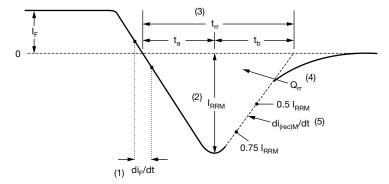


Fig. 8 - Typical dI<sub>(rec)M</sub>/dt vs. dI<sub>F</sub>/dt



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current

1000

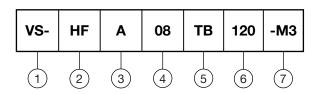
- (3)  $t_{\rm rr}$  reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$ and  $\rm I_{RRM}$ 
  - $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (5)  $di_{(rec)M}/dt$  peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions



#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

- HEXFRED® family

3 - Electron irradiated

- Current rating (08 = 8 A)

5 - Package:

TB = 2L TO-220AC

6 - Voltage rating (120 = 1200 V)

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

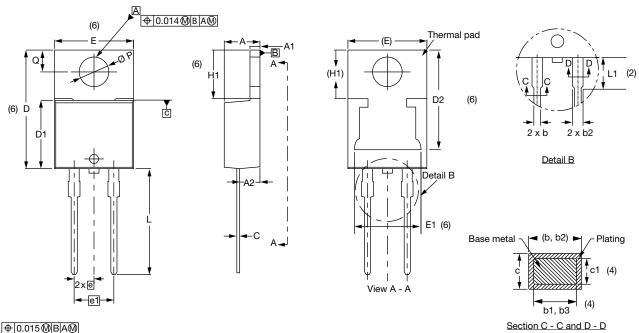
ORDERING INFORMATION (Example)								
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION						
VS-HFA08TB120-M3	50	Antistatic plastic tube						

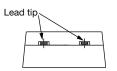
LINKS TO RELATED DOCUMENTS							
Dimensions <u>www.vishay.com/doc?96156</u>							
Part marking information	www.vishay.com/doc?95391						



## **TO-220AC 2L**

#### **DIMENSIONS** in millimeters and inches





Conforms to JEDEC® outline TO-220AC

SYMBOL	MILLIM	IETERS	ERS INCHES NOTES	SYMBOL MILLIMETER		IETERS	ERS INCHES					
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			Е	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355				•	•			

#### **Notes**

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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